

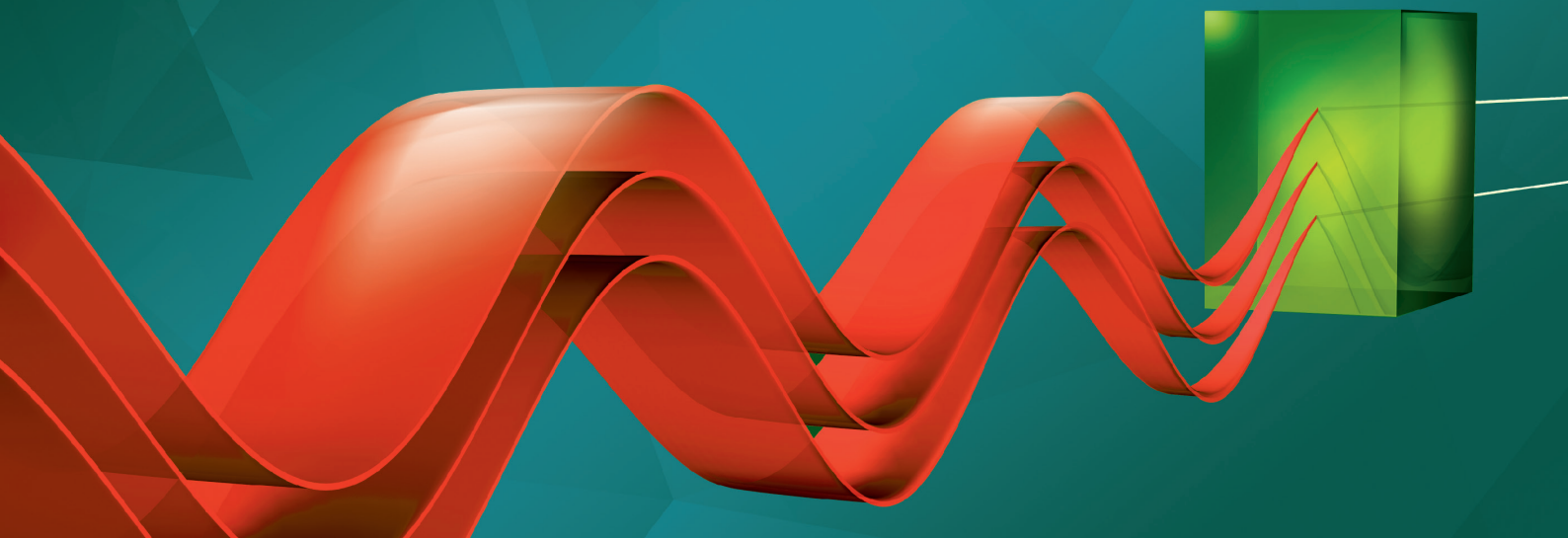
电力电子、智能运动、可再生能源
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Renewable Energy and Energy Management

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Proceedings

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Power for Efficiency!



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Dear PCIM Asia participants,

It's my great pleasure to invite all of you to the PCIM Asia Conference and Exhibition 2020 in Shanghai.

I am very happy that this year we are having an outstanding high level technical program in complimentary to 3 leading experts for keynote presentations and 4 poster sessions. The PCIM is targeting important innovations in the field of power electronics system engineering, the new generation of power devices and packaging technologies. For companies the PCIM is the worldwide leading event to launch new components and power conversion units in the market. Power electronic experts and scientist are presenting their latest research results during the conference. Decision makers from companies and academia use the PCIM platform to generate new market segments and trigger future research directions. Within the last decade power electronics technology has become the driving forces for many new fields of applications such as all electric transportation systems, future renewable energy technologies and factory automation systems. The PCIM Asia Conference and Exhibition serves as a technical and scientific platform for engineers and researchers engaged in all fields of power electronics starting from power components, power converter technologies, and future smart control systems.



Innovative products displayed and discussed during the PCIM Conference

The exciting technical program of this year's PCIM is addressing the next generation of power devices with a strong focus on wide bandgap material and the latest research results on advanced digital controlled power converters for industry and automotive applications. Further highlights will be design considerations for ultrafast switching devices and advanced packaging technologies.

Key development trends along the power electronics roadmap

In the keynote presentations this year we are highlighting development trends for advanced control of distributed energy source converters, the power device roadmap for electric vehicle including charging infrastructure technologies and new developments for SiC devices gate driver operating in high power density DC/DC converters. Distinguished speakers will be discussing power converters for high-speed railway traction applications. As a further highlight this year we implemented a tutorial on future modular multilevel converters.

The Young Engineer and Best Paper Award will be announced during the PCIM Asia Conference 2020 – this is certainly one of the highlights of the conference.

I am very excited having the opportunity to interact with the power electronics experts around the globe and look forward to sharing with all of you an outstanding and successful high level technical conference in Shanghai.

Leo Lorenz

General Conference Director, Germany

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Luo	Xiaorong	University of Electronic Science and Technology of China	CN
Luo	Haihui	Zhuzhou CRRC Times Semiconductor	CN
Luo	Peng	University of Sheffield	UK

M

Ma	Xin	Infineon Integrated Circuit (Beijing)	CN
Mademlis	Christos	Aristotle University of Thessaloniki	GR
Meissner	Michael	Helmut Schmidt University	DE
Meng	Yanjing	Shanxi University of Science & Technology	CN

N

Ng	Wai Tung	University of Toronto	CA
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P			
Papagiannis	Dimitrios	Aristotle University of Thessaloniki	GR
Peng	Yongdian	Zhuzhou CRRC Times Semiconductor	CN
Preuss	Elisabeth	Infineon Technologies	DE
Q			
Qiao	Lifeng	Delta Electronics (Shanghai)	CN
Qin	Guangyuan	Zhuzhou CRRC Times Semiconductor	CN
Qin	Rongzhen	Zhuzhou CRRC Times Semiconductor	CN
Qiu	Jianwen	Semikron Electronics (Zhuhai)	CN
R			
Raffo	Diego	Infineon Technologies	US
Rai	Shishir	DiscoverEE	US
Ren	Lintao	Shanghai University	CN
S			
Saito	Shota	Mitsubishi Electric	JP
Saito	Wataru	Kyushu University	JP
Sakai	Junya	Mitsubishi Electric	JP
Santos	Pedro dos	TU Kaiserslautern	DE
Sasaki	Masahiro	Fuji Electric	JP
Schilling	Uwe	Semikron Elektronik	DE
Sekino	Yusuke	Fuji Electric	JP
Sewergin	Alexander	ISEA – RWTH Aachen University	DE
Shi	Tianling	Shanghai University	CN
Shi	Simon	Infineon Technologies	CN
Shi	Rongliang	Guilin University of Technology	CN

Shiigi	Takashi	Fuji Electric	JP
Siebenhuhnner	Matthew	MacDermid Alpha Electronics Solutions	US
Singh	Richa	Power Integrations	DE
Sobe	Klaus	Infineon Technologies	AT
Song	Gaosheng	Mitsubishi Electric & Electronics (Shanghai)	CN
Song	Jianguo	Shanghai Maritime University	CN
Song	Jinsheng	Infineon Technologies	US
Spang	Matthias	Semikron Elektronik	DE
Stippich	Alexander	ISEA – RWTH Aachen University	DE
Su	Jianzhong	JingChuan Electronic Technology Development	CN
Su	Zhisheng	Maxsine Electric	CN
Sun	Jian	Mitsubishi Electric & Electronics (Shanghai)	CN
Sun	Huibo	Infineon Integrated Circuit (Beijing)	CN
Susanti	Liliyani	MacDermid Alpha Electronics Solutions	DE
Suyama	Taikei	National Institute of Technology, Akashi College	JP

T

Takaku	Taku	Fuji Electric	JP
Takei	Manabu	Fuji Electric	JP
Tamai	Yuuta	Fuji Electric	JP
Tang	Tianhao	Shanghai Maritime University	CN
Tang	Longgu	Zhuzhou CRRC Times Semiconductor	CN
Teng	Yuan	Zhuzhou CRRC Times Semiconductor	CN
Tsioumas	Evangelos	Aristotle University of Thessaloniki	GR
Tsuji	Takashi	Fuji Electric	JP
Tsyplakov	Evgeny	ABB Power Grids Switzerland	CH

U

Usui	Ryosuke	Fuji Electric	JP
Utsumi	Makoto	Fuji Electric	JP

V

Vázquez	Mateo	TU Kaiserslautern	DE
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W

Wang	Chenchen	Beijing Jiaotong University	CN
Wang	Heng	Infineon Integrated Circuit (Beijing)	CN
Wang	Fei	Shanghai University	CN
Wang	Gaolin	Harbin Institute of Technology	CN

Wang	Hao	Power Integrations	CN
Wang	Mengqi	University of Toronto	CA
Wang	Runze	University of Electronic Science and Technology of China	CN
Wang	Hui	Zhuzhou CRRRC Times Semiconductor	CN
Wang	Zhenye	Shanghai University	CN
Wen	Chunxue	North China University of Technology	CN
Wienhausen	Arne H.	ISEA – RWTH Aachen University	DE
Wu	Wilson	MacDermid Alpha Electronics Solutions	CN
Wu	Yibo	Zhuzhou CRRRC Times Semiconductor	CN
Wu	Bruce	Infineon Technologies	CN
X			
Xiang	Danyi	Fuji Electric	CN
Xiao	Haibo	Zhuzhou CRRRC Times Semiconductor	CN
Xiao	Qiang	Zhuzhou CRRRC Times Semiconductor	CN
Xin	Xiong	China Academy of Engineering Physics	CN
Xiong	Qi	North China University of Technology	CN
Xu	Ninghua	Zhuzhou CRRRC Times Semiconductor	CN
Xu	Dianguo	Harbin Institute of Technology	CN
Y			
Yamazaki	Tomoyuki	Fuji Electric	JP
Yan	Jichi	Guilin University of Technology	CN
Yang	Yong	Infineon Integrated Circuit (Beijing)	CN
Yang	Hailong	Inventchip Technology	CN
Yano	Hiroshi	University of Tsukuba	JP
Yao	Yao	Zhuzhou CRRRC Times Semiconductor	CN
Ye	Pan	Maxsine Electric	CN
Ye	Zhong	Inventchip Technology	CN
Yin	Shan	China Academy of Engineering Physics	CN
Ying	Jianping	Delta Electronics (Shanghai)	CN
Yoshida	Keniti	Fuji Electric	JP
Yu	Wei	Zhuzhou CRRRC Times Semiconductor	CN
Yu	Jingshu	University of Toronto	CA
Yu	Yannan	Guilin University of Technology	CN
Yuan	Tianshu	Institute of Electrical Engineering Chinese Academy of Sciences	CN

Z

Zeng	Xiong	Zhuzhou CRRC Times Semiconductor	CN
Zhang	Zisui	Beijing Jiaotong University	CN
Zhang	Weijia	University of Toronto	CA
Zhang	Zhonghua	Zhuzhou CRRC Times Semiconductor	CN
Zhang	Haoliang	Zhuzhou CRRC Times Semiconductor	CN
Zhang	Hongbo	Mitsubishi Electric	JP
Zhang	Dehui	Delta Electronics (Shanghai)	CN
Zhang	Lijun	Shanghai University	CN
Zhang	Wenjing	ON Semiconductor	CN
Zhang	XianKun	Zhuzhou CRRC Times Semiconductor	CN
Zhang	Zhixue	CRRC Zhuzhou Institute	CN
Zhao	Jia	Infineon Integrated Circuit (Beijing)	CN
Zhao	Lizhong	Mitsubishi Electric & Electronics (Shanghai)	CN
Zhao	Nannan	Harbin Institute of Technology	CN
Zhao	Rui	Mitsubishi Electric & Electronics (Shanghai)	CN
Zhou	Minglei	Beijing Jiaotong University	CN
Zhou	Xichao	State Grid Integrated Energy Service	CN
Zhou	Jinghua	North China University of Technology	CN
Zhu	Dan	Semikron Electronics (Zhuhai)	CN